













CSD18534Q5A

SLPS389D -OCTOBER 2012-REVISED JUNE 2015

CSD18534Q5A 60 V N-Channel NexFET™ Power MOSFET

Features

- Ultra-Low Qa and Qad
- Low Thermal Resistance
- Avalanche Rated
- Logic Level
- Pb Free Terminal Plating
- **RoHS Compliant**
- Halogen Free
- SON 5 mm x 6 mm Plastic Package

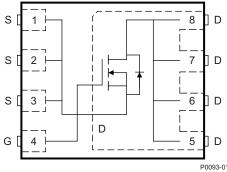
Applications

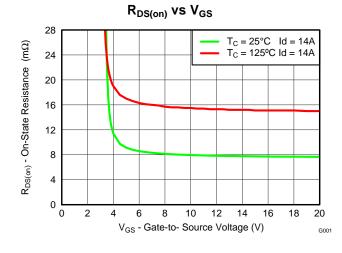
- DC-DC Conversion
- Secondary Side Synchronous Rectifier
- Isolated Converter Primary Side Switch
- Motor Control

Description

This 7.8 mΩ, 60 V, SON 5 × 6 mm NexFET[™] power MOSFET is designed to minimize losses in power conversion applications.







Product Summary

$T_A = 25^\circ$	С	TYPICAL VA	UNIT		
V_{DS}	Drain-to-source voltage	60	٧		
Q_g	Gate charge total (10 V)	17		nC	
Q_{gd}	Gate charge gate-to-drain 3.5				
В	Drain-to-source on-resistance	V _{GS} = 4.5 V	9.9	mΩ	
R _{DS(on)}	Diam-to-source on-resistance	V _{GS} = 10 V 7.8		mΩ	
$V_{GS(th)}$	Threshold voltage	1.9	V		

Ordering Information⁽¹⁾

DEVICE	QTY	MEDIA	PACKAGE	SHIP
CSD18534Q5A	2500	13-Inch Reel	SON 5 mm × 6 mm	Tape and
CSD18534Q5AT	250	7-Inch Reel	Plastic Package	Reel

For all available packages, see the orderable addendum at the end of the data sheet.

Absolute Maximum Ratings

710001d10 Maximum Hatingo								
$T_A = 2$	5°C	VALUE	UNIT					
V_{DS}	Drain-to-source voltage	60	٧					
V_{GS}	Gate-to-source voltage	±20	V					
I _D	Continuous drain current (package limited)	50						
	Continuous drain current (silicon limited), T _C = 25°C	69	Α					
	Continuous drain current, T _A = 25°C ⁽¹⁾	13						
I _{DM}	Pulsed drain current, T _A = 25°C ⁽²⁾	229	Α					
п	Power dissipation ⁽¹⁾	3.1	10/					
P _D	Power dissipation, T _C = 25°C	77	W					
T _J , T _{stg}	Operating junction, Storage temperature	-55 to 150	°C					
E _{AS}	Avalanche energy, single pulse $I_D = 40 \text{ A}, L = 0.1 \text{mH}, R_G = 25 \Omega$	80	mJ					

- (1) Typical $R_{\theta JA}=40^{\circ} C/W$ on a 1 inch², 2 oz. Cu pad on a 0.06 inch thick FR4 PCB.
- (2) Max R_{θ,IC} = 2.0°C/W, pulse duration ≤100 μs, duty cycle ≤1%

Gate Charge

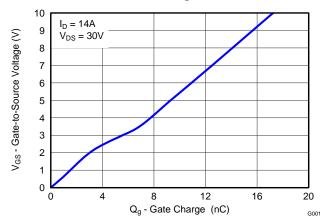




Table of (Contents
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1 Features 1 2 Applications 1 3 Description 1 4 Revision History 2 5 Specifications 3 5.1 Electrical Characteristics 3 5.2 Thermal Information 3 5.3 Typical MOSFET Characteristics 4 6 Device and Documentation Support 7	6.1 Community Resources
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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision C (August 2014) to Revision D	Page
Changed description to read 60 V Added Community Resources	
Changes from Revision B (July 2014) to Revision C	Page
Added 7-inch reel to Ordering Information table	
Increased pulsed current to 229 A	1
Updated the SOA in Figure 10	6
Changes from Revision A (January 2013) to Revision B	Page
Added parameter for power dissipation with case temperature held to 25°C	1
Updated pulsed current conditions	1
Updated Figure 1 to a normalized R _{eJC} curve	4
Changes from Original (October 2012) to Revision A	Page
Changed g _c . Transconductance from: 122 to: 72	3

Product Folder Links: CSD18534Q5A



5 Specifications

5.1 Electrical Characteristics

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
STATIC	CHARACTERISTICS	'			'	
BV _{DSS}	Drain-to-source voltage	V _{GS} = 0 V, I _D = 250 μA	60			V
I _{DSS}	Drain-to-source leakage current	V _{GS} = 0 V, V _{DS} = 48 V			1	μA
I _{GSS}	Gate-to-source leakage current	V _{DS} = 0 V, V _{GS} = 20 V			100	nA
V _{GS(th)}	Gate-to-source threshold voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1.5	1.9	2.3	V
	Dunin to common or unninteres	V _{GS} = 4.5 V, I _D = 14 A		9.9	12.4	mΩ
R _{DS(on)}	Drain-to-source on-resistance	V _{GS} = 10 V, I _D = 14 A		7.8	9.8	mΩ
9 _{fs}	Transconductance	V _{DS} = 30 V, I _D = 14 A		72		S
DYNAMI	C CHARACTERISTICS	,	•		,	
C _{iss}	Input capacitance			1360	1770	pF
C _{oss}	Output capacitance	$V_{GS} = 0 \text{ V}, V_{DS} = 30 \text{ V}, f = 1 \text{ MHz}$		167	217	pF
C _{rss}	Reverse transfer capacitance			5	6.5	pF
R_G	Series gate resistance			1.5	3	Ω
Qg	Gate charge total (4.5 V)			8.5	11.1	
Qg	Gate charge total (10 V)			17	22	nC
Q _{gd}	Gate charge gate-to-drain	V _{DS} = 30 V, I _D = 14 A		3.5		nC
Q _{gs}	Gate charge gate-to-source			3.2		nC
Q _{g(th)}	Gate charge at V _{th}			2.6		nC
Q _{oss}	Output charge	V _{DS} = 30 V, V _{GS} = 0 V		19		nC
t _{d(on)}	Turn on delay time			5.2		ns
t _r	Rise time	V 20 V V 40 V I 44 A B 0 0		5.5		ns
t _{d(off)}	Turn off delay time	$V_{DS} = 30 \text{ V}, V_{GS} = 10 \text{ V}, I_{DS} = 14 \text{ A}, R_G = 0 \Omega$		15		ns
t _f	Fall time			2		ns
DIODE C	CHARACTERISTICS	· · · · · · · · · · · · · · · · · · ·				
V _{SD}	Diode forward voltage	I _{SD} = 14 A, V _{GS} = 0 V		8.0	1	V
Q _{rr}	Reverse recovery charge	V 20 V I 44 A di/dt 200 A/v-		54		nC
t _{rr}	Reverse recovery time	V_{DS} = 30 V, I_F = 14 A, di/dt = 300 A/ μ s		40		ns

5.2 Thermal Information

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

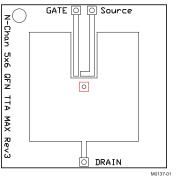
	THERMAL METRIC	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction-to-case thermal resistance (1)			2.0	°C/W
$R_{\theta JA}$	Junction-to-ambient thermal resistance ⁽¹⁾⁽²⁾			50	°C/W

⁽¹⁾ R_{θJC} is determined with the device mounted on a 1 inch² (6.45 cm²), 2 oz. (0.071 mm thick) Cu pad on a 1.5 inches x 1.5 inches (3.81 cm x 3.81 cm), 0.06 inch (1.52 mm) thick FR4 PCB. R_{θJC} is specified by design, whereas R_{θJA} is determined by the user's board design.

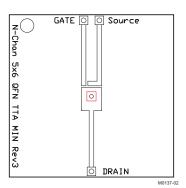
(2) Device mounted on FR4 material with 1 inch2 (6.45 cm2), 2 oz. (0.071 mm thick) Cu.

Product Folder Links: CSD18534Q5A





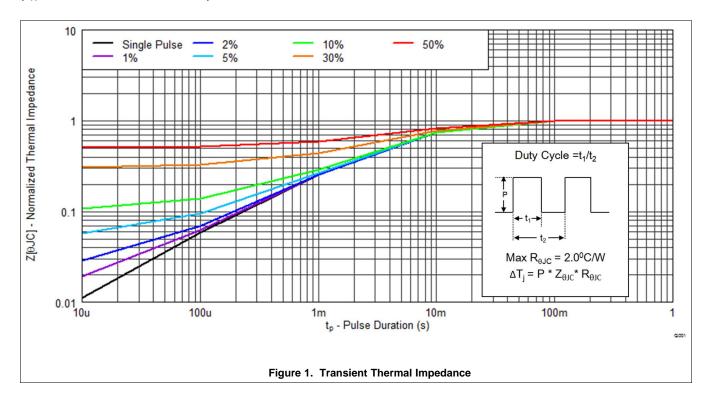
Max $R_{\theta JA} = 50^{\circ} C/W$ when mounted on 1 inch² (6.45 cm²) of 2 oz. (0.071 mm thick) Cu.



Max $R_{\theta JA} = 125^{\circ} C/W$ when mounted on a minimum pad area of 2 oz. (0.071 mm thick) Cu.

5.3 Typical MOSFET Characteristics

(T_A = 25°C unless otherwise stated)



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G001



60

40

20

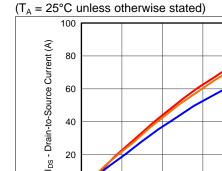
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0

0.2

0.4

Typical MOSFET Characteristics (continued)



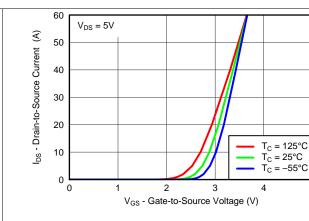


Figure 2. Saturation Characteristics

0.6

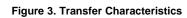
V_{DS} - Drain-to-Source Voltage (V)

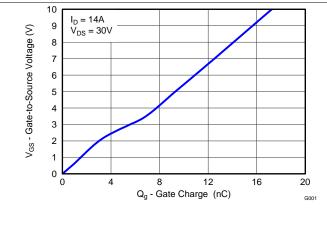
8.0

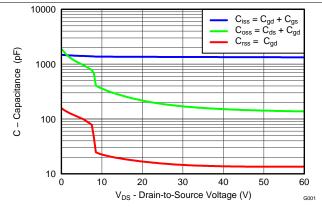
V_{GS} =10V

V_{GS} =6.5V $V_{GS} = 4.5V$

1.2









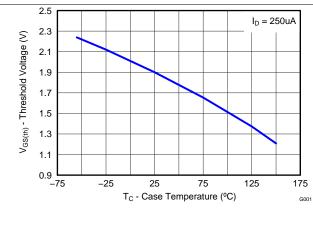


Figure 6. Threshold Voltage vs Temperature

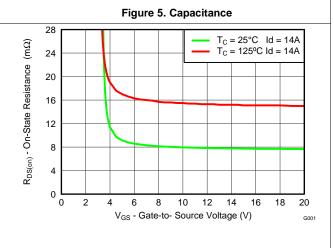
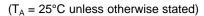
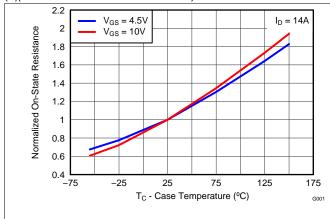


Figure 7. On-State Resistance vs Gate-to-Source Voltage



Typical MOSFET Characteristics (continued)





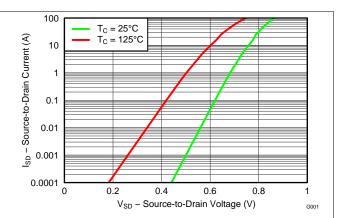
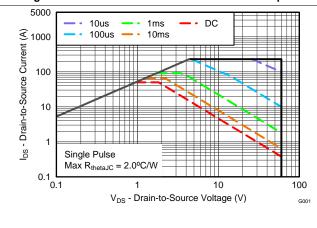


Figure 8. Normalized On-State Resistance vs Temperature





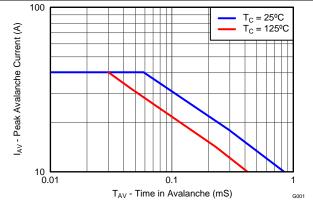


Figure 10. Maximum Safe Operating Area

Figure 11. Single Pulse Unclamped Inductive Switching

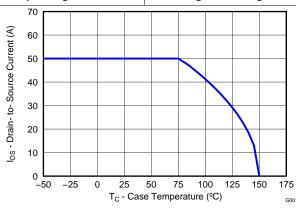


Figure 12. Maximum Drain Current vs Temperature

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6 Device and Documentation Support

6.1 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Lise

TI E2E™ Online Community TI's Engineer-to-Engineer (E2E) Community. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

6.2 Trademarks

NexFET, E2E are trademarks of Texas Instruments.

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6.3 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

6.4 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

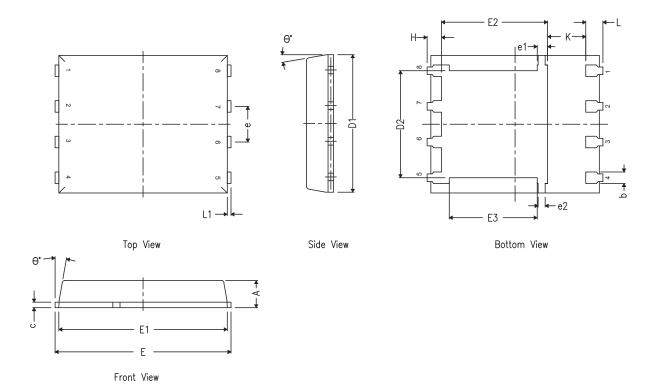
Product Folder Links: CSD18534Q5A



7 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

7.1 Q5A Package Dimensions



DIM		MILLIMETERS	
DIM	MIN	NOM	MAX
Α	0.90	1.00	1.10
b	0.33	0.41	0.51
С	0.20	0.25	0.34
D1	4.80	4.90	5.00
D2	3.61	3.81	4.02
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	3.38	3.58	3.78
E3	3.03	3.13	3.23
е	1.17	1.27	1.37
e1	0.27	0.37	0.47
e2	0.15	0.25	0.35
Н	0.41	0.56	0.71
K	1.10	_	_
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
θ	0°	_	12°

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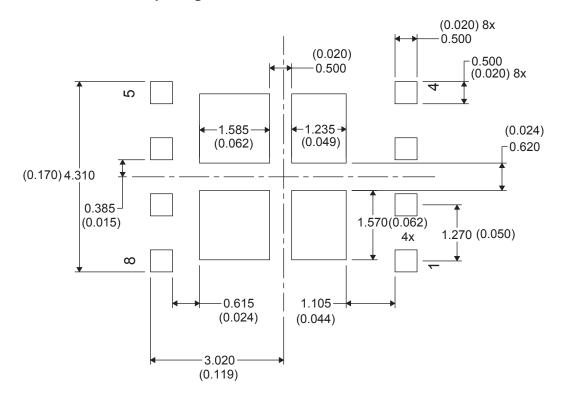
7.2 Recommended PCB Pattern

Recommended PCB Pattern (continued)

DIM	MILLIME	TERS	INC	HES
DIM	MIN	MAX	MIN	MAX
F1	6.205	6.305	0.244	0.248
F2	4.46	4.56	0.176	0.18
F3	4.46	4.56	0.176	0.18
F4	0.65	0.7	0.026	0.028
F5	0.62	0.67	0.024	0.026
F6	0.63	0.68	0.025	0.027
F7	0.7	0.8	0.028	0.031
F8	0.65	0.7	0.026	0.028
F9	0.62	0.67	0.024	0.026
F10	4.9	5	0.193	0.197
F11	4.46	4.56	0.176	0.18

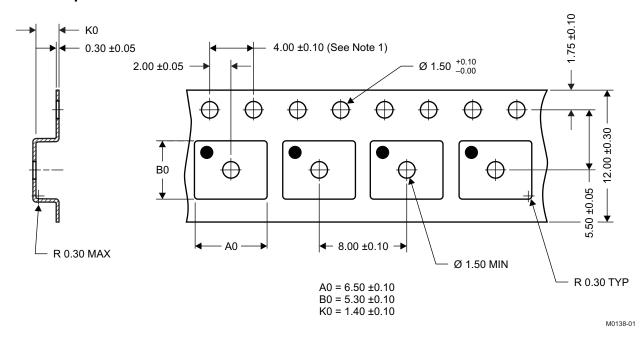
For recommended circuit layout for PCB designs, see application note *Reducing Ringing Through PCB Layout Techniques*, SLPA005.

7.3 Recommended Stencil Opening





7.4 Q5A Tape and Reel Information



Notes:

- 1. 10-sprocket hole-pitch cumulative tolerance ±0.2
- 2. Camber not to exceed 1 mm in 100 mm, noncumulative over 250 mm
- 3. Material: black static-dissipative polystyrene
- 4. All dimensions are in mm (unless otherwise specified).
- 5. A0 and B0 measured on a plane 0.3 mm above the bottom of the pocket.

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PACKAGE OPTION ADDENDUM

29-May-2015

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
CSD18534Q5A	ACTIVE	VSONP	DQJ	8	•	Pb-Free (RoHS Exempt)	. , ,	Level-1-260C-UNLIM	-55 to 150	CSD18534	Samples
CSD18534Q5AT	ACTIVE	VSONP	DQJ	8	250	Pb-Free (RoHS Exempt)	CU SN	Level-1-260C-UNLIM	-55 to 150	CSD18534	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

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Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OPTION ADDENDUM

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